SKiiP 03NEB066V1 ...



MiniSKiiP[®] 1

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SKIIP 03NEB066V1

Target Data

Features

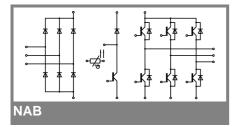
- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

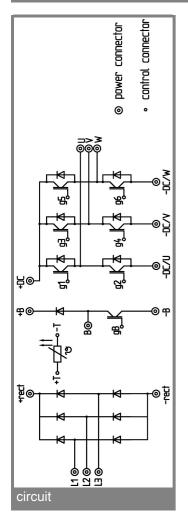
- Inverter up to 5,6 kVA
- Typical motor power 3,0 kW

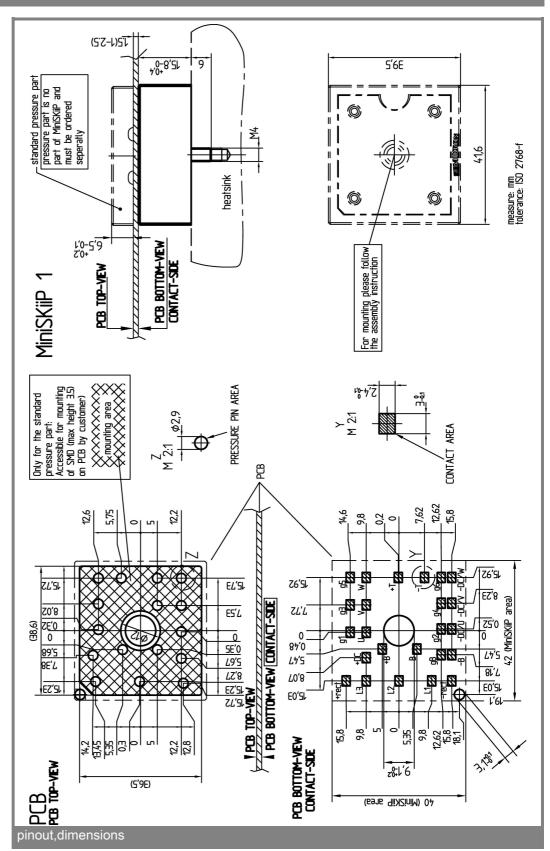
Absolute	Maximum Ratings	T _s = 25 °C, unless otherwise specified					
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V_{CES}		600	V				
I _C	T _s = 25 (70) °C		Α				
I _{CRM}	$T_s = 25 (70) ^{\circ}C, t_p \le 1 \text{ms}$		Α				
V_{GES}		± 20	V				
T_j		- 40 + 150	°C				
Diode - Inverter, Chopper							
I _F	T _s = 25 (70) °C		Α				
I _{FRM}	$T_s = 25 (70) ^{\circ}C, t_p \le 1 \text{ms}$		Α				
T _j		- 40 + 150	°C				
Diode - Rectifier							
V_{RRM}		800	V				
I _F	T _s = 70 °C	35	Α				
I _{FSM}	$t_p = 10 \text{ ms, sin } 180 ^\circ, T_j = 25 ^\circ\text{C}$	220	Α				
i²t	$t_p = 10 \text{ ms, sin } 180 ^\circ, T_j = 25 ^\circ\text{C}$	240	A²s				
T _j		- 40 + 150	°C				
I _{tRMS}	per power terminal (20 A / spring)	20	Α				
T_{stg}	$T_{op} \le T_{stg}$	- 40 + 125	°C				
V _{isol}	AC, 1 min.	2500	V				

Characteristics		$\Gamma_{\rm s}$ = 25 °C, unless otherwise specified						
Symbol	Conditions	min.	typ.	max.	Units			
IGBT - Inverter, Chopper								
V_{CEsat}	I _C = 15 A, T _j = 25 (125) °C		2 (2,2)	2,5 (2,7)	V			
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0.5 \text{ mA}$	3	4	5	V			
$V_{CE(TO)}$	$T_j = 25 (125) ^{\circ}C$		1,2 (1,1)	1,3 (1,2)	V			
r _T	$T_j = 25 (125) ^{\circ}C$		53 (73)	80 (100)	mΩ			
C _{ies}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,77		nF			
C _{oes}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,12		nF			
C _{res}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,66		nF			
$R_{th(j-s)}$	per IGBT		1,4		K/W			
t _{d(on)}	under following conditions		20		ns			
t _r	$V_{CC} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}$		30		ns			
t _{d(off)}	$I_C = 15 \text{ A}, T_j = 125 ^{\circ}\text{C}$		195		ns			
t _f	$R_{Gon} = R_{Goff} = 50 \Omega$		10		ns			
E _{on}	inductive load		0,55		mJ			
E _{off}			0,24		mJ			
	Diode - Inverter, Chopper							
$V_F = V_{EC}$	I _F = 15 A, T _j = 25 (125) °C		1,4 (1,4)	1,7 (1,7)	V			
$V_{(TO)}$	T _j = 25 (125) °C		1 (0,9)	1,1 (1)	V			
r _T	$T_j = 25 (125) °C$		30 (33)	40 (47)	mΩ			
$R_{th(j-s)}$	per diode		2,2		K/W			
I _{RRM}	under following conditions		22		Α			
Q_{rr}	I _F = 15 A, V _R = 300 V		1,5		μC			
E _{rr}	V _{GE} = 0 V, T _j = 125 °C		0,31		mJ			
	$di_F/dt = 1100 A/\mu s$							
Diode - R	Diode - Rectifier							
V_{F}	I _F = 15 A, T _i = 25 °C		1,1		V			
$V_{(TO)}$	T _j = 150 °C		0,8		V			
r _T	$T_{j} = 150 ^{\circ}C$		20		mΩ			
$R_{th(j-s)}$	per diode		1,5		K/W			
	ture Sensor							
R _{ts}	3 %, T _r = 25 (100) °C		1000(1670)		Ω			
Mechanical Data								
w			35		g			
M_s	Mounting torque	2		2,5	Nm			



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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